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2 ABSTRACT OF THE DISCLOSURE

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4 A method for maximizing the interfacial properties of
5 magnetoresistive sensors, such as spin valve and GMR sensors used
6 in storage devices, comprises selecting the materials for
7 ferromagnetic layers and for electrically conductive spacers that
8 are interposed between the ferromagnetic layers. The
9 electronegativities of the selected materials are substantially
10 matched so that an absolute value of the differences in
11 electronegativities is minimized. The conductive spacer material
12 provides a relatively low resistivity and a large mean free path.

13 The sensors experience greater chemical and thermal stability,
14 are corrosion resistant, and realize an increased signal output.

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